

L Number	Hits	Search Text	DB	Time stamp
1	28	250/49\$.ccls. and ion adj beam and align\$5 and mask and slit and density	USPAT; EPO; JPO; DERWENT	2004/06/29 12:58
2	19	(250/49\$.ccls. and ion adj beam and align\$5 and mask and slit and density) and density with ion	USPAT; EPO; JPO; DERWENT	2004/06/29 10:39
3	0	(250/49\$.ccls. and ion adj beam and align\$5 and mask and slit and density) and density with ion with hole	USPAT; EPO; JPO; DERWENT	2004/06/29 10:39
4	53	250/49\$.ccls. and ion adj beam and align\$5 and mask and slit	USPAT; EPO; JPO; DERWENT	2004/06/29 11:17
5	44	(250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/06/29 11:18
7	0	((250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole same desinty	USPAT; EPO; JPO; DERWENT	2004/06/29 10:55
8	1	((250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole same density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:18
6	7	((250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole	USPAT; EPO; JPO; DERWENT	2004/06/29 11:20
9	38	250/\$.ccls. and ion adj beam and align\$5 and mask and slit and density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:17
10	365	ion adj beam and align\$5 and mask and slit	USPAT; EPO; JPO; DERWENT	2004/06/29 11:29
11	83	(ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)	USPAT; EPO; JPO; DERWENT	2004/06/29 11:17
12	73	((ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/06/29 11:20
13	10	((ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)) and plate\$5) and plate\$5 same hole same density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:18
14	295	(ion adj beam and align\$5 and mask and slit) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/06/29 11:20
15	93	((ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole	USPAT; EPO; JPO; DERWENT	2004/06/29 11:20
16	80	((ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole) and density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:21
17	354	ion adj beam and align\$5 and mask and slit and (substrate wafer)	USPAT; EPO; JPO; DERWENT	2004/06/29 11:29
18	12	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and hole with density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:38
19	36	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and hole same density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:35
20	25	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and aperture same density	USPAT; EPO; JPO; DERWENT	2004/06/29 11:38
21	90	250/49\$.ccls. and beam same density and mask and slit	USPAT; EPO; JPO; DERWENT	2004/06/29 12:59

22	33	250/49\$.ccls. and beam same density same (hole aperture) and mask and slit	USPAT; EPO; JPO; DERWENT	2004/06/29 12:59
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